

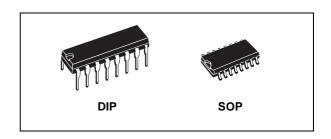
HCF4053B

TRIPLE 2-CHANNEL ANALOG MULTIPLEXER

- LOW "ON" RESISTANCE : 125Ω (Typ.) OVER 15V p.p SIGNAL-INPUT RANGE FOR V_{DD} - V_{EE} = 15V
- HIGH "OFF" RESISTANCE : CHANNEL LEAKAGE ± 100pA (Typ.) at V_{DD} V_{EE} = 18V
- BINARY ADDRESS DECODING ON CHIP
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. at f_{IS} = 1KHz, V_{IS} = 5 V_{pp} , V_{DD} V_{SS} ≥ 10V, RL = 10K Ω
- VERY LOW QUIESCENT POWER DISSIPATION UNDER ALL DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS: 0.2 µW (Typ.) at V_{DD} - V_{SS} = V_{DD} - V_{EE} =10V
- MATCHED SWITCH CHARACTERISTICS : $R_{ON} = 5Ω$ (Typ.) FOR $V_{DD} V_{EE} = 15V$
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS: DIGITAL 3 to 20, ANALOG TO 20V p.p.
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT
 I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

The HCF4053B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor



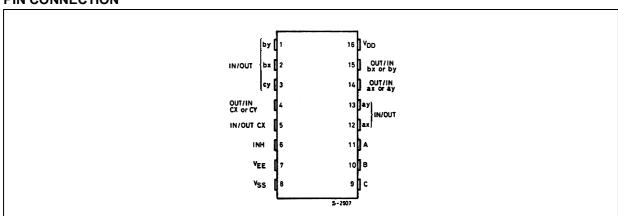
ORDER CODES

PACKAGE	TUBE	T&R
DIP	HCF4053BEY	
SOP	HCF4053BM1	HCF4053M013TR

technology available in DIP and SOP packages. The HCF4053B analog multiplexer/demultiplexer is a digitally controlled analog switch having low ON impedance and very low OFF leakage current. This multiplexer circuit dissipate extremely low quiescent power over the full $\rm V_{DD}$ - $\rm V_{SS}$ and $\rm V_{DD}$ - $\rm V_{EE}$ supply voltage range, independent of the logic state of the control signals.

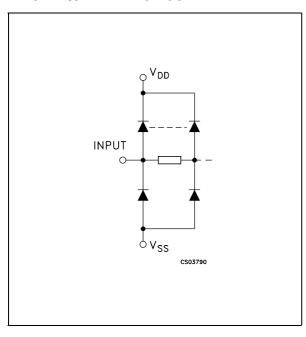
When a logic "1" is present at the inhibit input terminal all channel are off. This device is a triple 2-channel multiplexer having three separate digital control inputs, A, B, and C, and an inhibit input. Each control input selects one of a pair of channels which are connected in a single pole double-throw configuration.

PIN CONNECTION



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INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

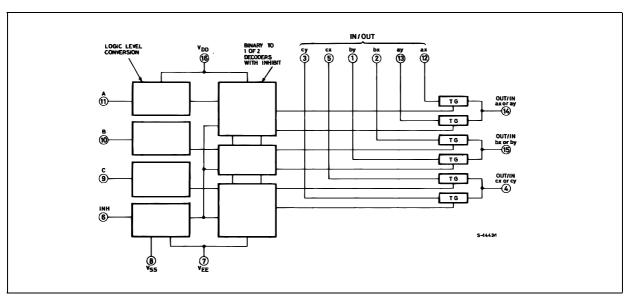
PIN No	SYMBOL	NAME AND FUNCTION
11, 10, 9	A, B, C	Binary Control Inputs
6	INH	Inhibit Inputs
12, 13, 2, 1, 5, 3	IN/OUT	ax,ay,bx,by,cx,cy Input/ Output
14	OUT/IN	ax or ay
15	OUT/IN	bx or by
4	OUT/IN	cx or cy
7	V_{EE}	Supply Voltage
8	V_{SS}	Negative Supply Voltage
16	V_{DD}	Positive Supply Voltage

TRUTH TABLE

INHIBIT	C or B or A	
0	0	ax or bx or cx
0	1	ay or by or cy
1	X	NONE

X : Don't Care

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
VI	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
l _l	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	500 (*)	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C

All voltage values are referred to VSS pin voltage. (*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65 °C to 85 °C

DC SPECIFICATIONS

		Test Condition			Value								
Symbol	Parameter	V _{IS}	V _{EE}	Vss	V _{DD}	Т	T _A = 25°C		-40 to 85°C		-55 to 125°C		Unit
		(V)	(V)	(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Device				5		0.04	5		150		150	
	Current (all				10		0.04	10		300		300	μA
	switches ON or all switches OFF)				15		0.04	20		600		600	μΑ
	ownorios or r j				20		0.08	100		3000		3000	
SWITCH													
R _{ON}	Resistance	0 <u><</u> V ₁ ≤			5		470	1050		1200		1200	
		V_{DD}	0	0	10		180	400		520		520	Ω
		- 00			15		125	280		360		360	
Δ_{ON}	Resistance Δ_{RON}	0 <u><</u> V _I ≤			5		10						
	(between any 2 of	V_{DD}	0	0	10		10						Ω
	4 switches)	• 00			15		5						
OFF*	Channel Leakage Current (All Channel OFF) (COMMON O/I)		0	0	18		±0.1	100		1000		1000	nA
OFF*	Channel Leakage Current (Any Channel OFF)		0	0	18		±0.1	100		1000		1000	nA
C _I	Input Capacitance						5						
Co	Output Capacitance		-5	-5	5		9						pF
C _{IO}	Feed through						0.2						
CONTRO	DL (Address or Inhi	bit)		l	l	1	1	l	l	1	1	1	l
V _{IL}	Input Low Voltage		V _{EE} =	= Voo	5			1.5		1.5		1.5	
				1KΩ	10			3		3		3	V
		= VDD	to \		15			4		4		4	
V _{IH}	Input High Voltage	thru 1ΚΩ		2μΑ	5	3.5			3.5		3.5		
			(on al	I OFF	10	7			7		7		V
			chan		15	11			11		11		
I _{IH,} I _{IL}	Input Leakage Current	V _I = 0/18V		18		±10 ⁻³	±0.1		±1		±1	μΑ	
C _I	Input Capacitance						5	7.5					рF

^{*} Determined by minimum feasible leakage measurement for automating testing.

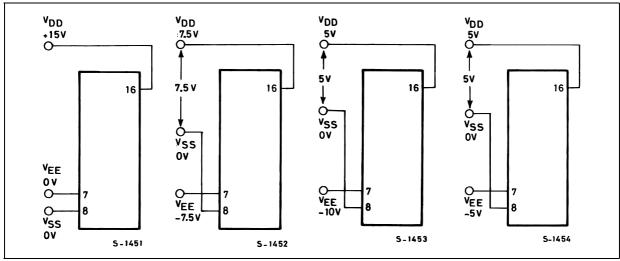
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_{L} = 50 pF$, all input square wave rise and fall time = 20 ns)

				Test Co	ndition				Value						
Parameter	V _{EE} (V)	R _L (ΚΩ)	f _I (KHz)	V _I (V)	V _{SS} (V)	V _{DD} (V)		Min.	Тур.	Max.					
Propagation Delay				V_{DD}		5			30	60					
Time (signal input to		200		V DD		10			15	30	ns				
output)						15			11	20					
Frequency Response Channel "ON" (sine	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		25		MHz				
wave input) at 20 log V _O /V _I = - 3dB	- * 55	•		3()		10	V _O at any channel		60		IVII IZ				
Feed through (all channels OFF) at	= V _{SS}	4		E (*)		10	V _O at Common OUT/IN		10		MIL				
$20 \log V_{O}/V_{I} = -40 dB$	- vss	1		5(*)		10	V _O at any channel		8		MHz				
Frequency Signal Crosstalk at	1/	4		F(*)		40	Between any 2 Sections (IN pin 2, OUT pin 14)		2.5		NAL I				
20 log V _O /V _I = -40dB	= V _{SS}	1				5(*)) (")	5()		10	Between any 2 Sections (IN pin 15, OUT pin 14)		6		MHz
0: 14				2(*)		5			0.3						
Sine Wave Distortion f _{IS} = 1KHz Sine Wave	= V _{SS}	3 10	1	3(*)		10			0.2		%				
IIIS - INTIZ Silie Wave				5(*)		15			0.12						
CONTROL (Address	or Inhibi	t)				•			•	•					
Propagation Delay:	0				0	5			360	720					
Address to Signal	0				0	10			160	320					
OUT (Channels ON or OFF)	0				0	15			120	240	ns				
	-5				0	5			225	450					
Propagation Delay:	0				0	5			360	720					
Inhibit to Signal OUT	0	4			0	10			160	320					
(Channel turning ON)	0	1			0	15			120	240	ns				
	-10				0	5			200	400					
Propagation Delay:	0					5			200	450					
Inhibit to Signal OUT	0	40				10			90	210					
(Channel turning	0	10				15			70	160	ns				
OFF)	-10					5			130	300	1				
Address or Inhibit to Signal Crosstalk	0	10 ⁽¹⁾			0	10	$V_C = V_{DD} - V_{SS}$ (square wave)		65		mV peak				

⁽¹⁾ Both ends of channel.

* Peak to Peak voltage symmetrical about (V_{DD} - V_{EE}) /2

TYPICAL BIAS VOLTAGES



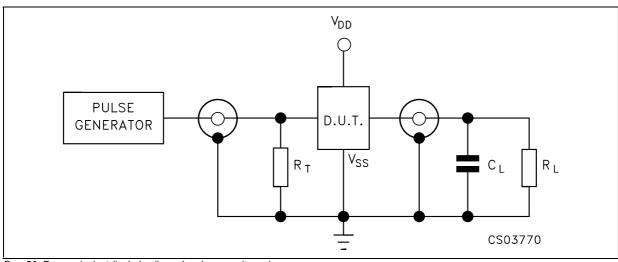
The ADDRESS (digital-control inputs) and INHIBIT logic levels are: "0"=V_{SS} and "1"=V_{DD}. The analog signal (through the TG) may swing from V_{EE} to V_{DD}

SPECIAL CONSIDERATIONS

Control of analog signals up to 20V peak to peak can be achieved by digital signal amplitudes of 4.5 to 20V (if V_{DD} - V_{SS} = 3V, a V_{DD} - V_{EE} of up to 13V can be controlled; for V_{DD} - V_{EE} level differences above 13V, a V_{DD} - V_{SS} of at least 4.5V is required. For example, if V_{DD} = +5, V_{SS} = 0, and V_{EE} = -13.5, analog signals from -13.5V to 4.5V can be controlled by digital inputs of 0 to 4.5V. In

certain applications, the external load resistor current may include both $\rm V_{\rm DD}$ and signal-line components. To avoid drawing $\rm V_{\rm DD}$ current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0,8V (calculated from RON values shown in DC SPECIFICATIONS). No V_{DD} current will flow through R_I if the switch current flows into leads 4, 14 and 15.

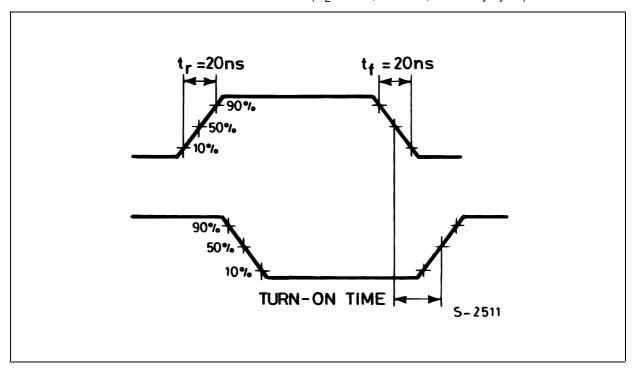
TEST CIRCUIT



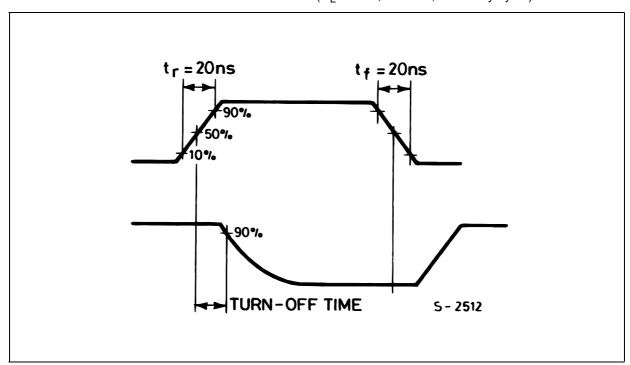
C_L = 50pF or equivalent (includes jig and probe capacitance)

 $R_L = 200 \text{K}\Omega$ $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1 : CHANNEL BEING TURNED ON ($R_L = 1K\Omega$, f=1MHz; 50% duty cycle)

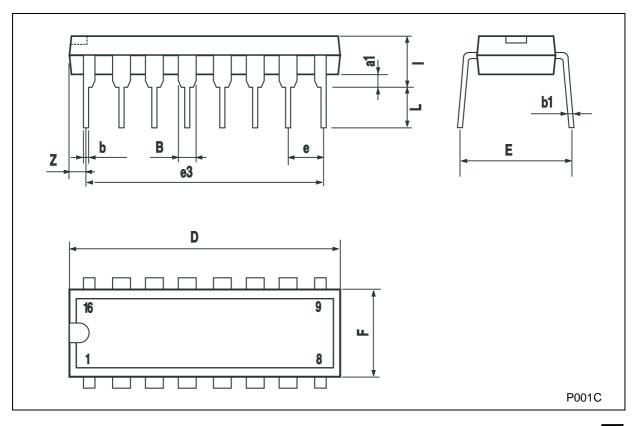


WAVEFORM 2 : CHANNEL BEING TURNED OFF (R_L = 1K Ω , f=1MHz; 50% duty cycle)



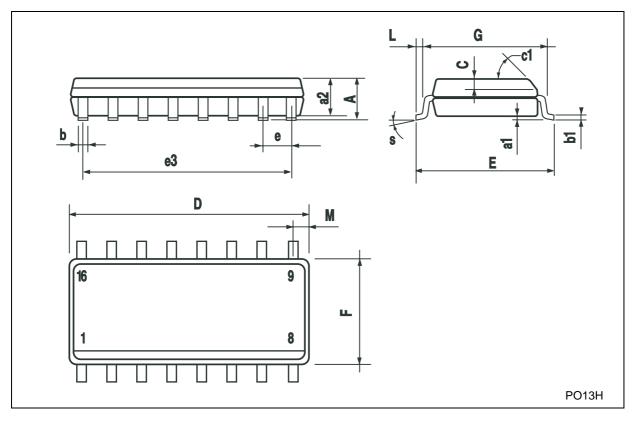
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
Е		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



SO-16 MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)		•		
D	9.8		10	0.385		0.393		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
M			0.62			0.024		
S			8° (ı	max.)				



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